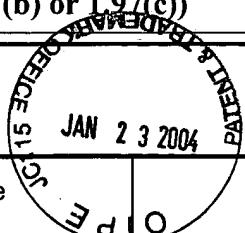


TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
SETI-0007

In Re Application: Shur et al.



Serial No.

10/696,693

Filing Date

10/29/2003

Examiner

Unknown

Group Art Unit

Unknown

METHOD OF RADIATION GENERATION AND MANIPULATION

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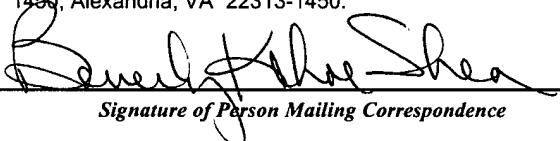
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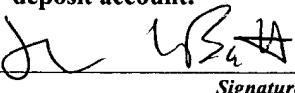


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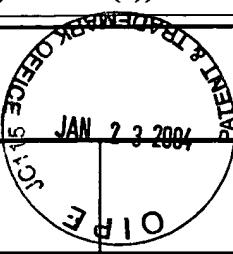
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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
SETI-0007

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Serial No.
10/696,693

Filing Date
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Examiner
Unknown

Group Art Unit
Unknown

Title: **METHOD OF RADIATION GENERATION AND MANIPULATION**

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37 CFR 1.97(b)

1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

the statement specified in 37 CFR 1.97(e);

OR

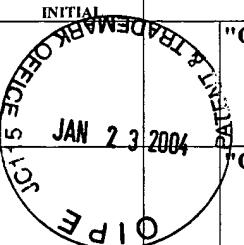
the fee set forth in 37 CFR 1.17(p).

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional) SETI-0007	Application Number 10/696,693
Applicant(s) Shur et al.	
Filing Date 10/29/2003	Group Art Unit Unkn wn

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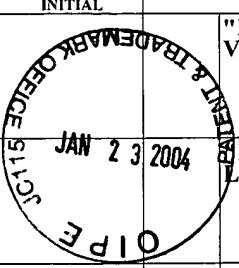
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	"Coherent THz Emission in Semiconductors," Semiconductors and Semimetals, Chapt. 8, Vol. 67, 2001, pp.389-440.
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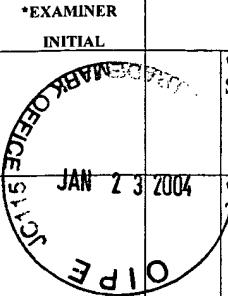
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		Applicant(s) Shur et al.	
		Filing Date 10/29/2003	Group Art Unit Unknown
*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
	<p>"Far Infrared Emission from Plasma Oscillations of Si Inversion Layers," D.C. Tsui et al., Solid State Communications, Vol. 35, 1980, pp. 875-877.</p> <p>"High Frequency Conductivity of the High-Mobility Two-Dimensional Electron Gas," P. J. Burke et al., Applied Physics Letters, Vol. 76, No. 6, February 2000, pp. 745-747.</p> <p>"A Resonant Terahertz Detector Utilizing a High Electron Mobility Transistor," J-Q. Lu et al., IEDM '98 Technical Digest, 1998, pp. 453-456.</p> <p>"Resonant Detection of Subterahertz Radiation by Plasma Waves in a Submicron Field-Effect Transistor," W. Knap et al., Applied Physics Letters, Vol. 80, No. 18, May 2002, pp. 3433-3435.</p> <p>"Terahertz Photoconductivity and Plasmon Modes in Double-Quantum-Well Field-Effect Transistors," X. G. Peralta et al., Applied Physics Letters, Vol. 81, No. 9, August 2002, pp. 1627-1629.</p> <p>"Ballistic FET as Tunable Terahertz Oscillator," M. Dyakonov et al., Proceedings of 2d International Semiconductor Device Research Symposium, Charlottesville, VA, December 1993, pp. 741-744.</p> <p>"Terahertz GaAs Devices and Circuits for Heterodyne Receiver Applications," T. Crowe et al., Compound Semiconductor Electronics The Age of Maturity: Selected Topics in Electronics and Systems, Vol. 4, 1996, pp. 209-245.</p> <p>"Materials for Terahertz Science and Technology," B. Ferguson et al., Nature Materials, Vol. 1, September 2002, pp. 26-33.</p> <p>"A Novel Schottky / 2-DEG Diode for Millimeter- and Submillimeter-Wave Multiplier Applications," W. C. B. Peatman et al., IEEE Electron Device Letters, Vol. 13, No. 1, January 1992, pp. 11-13.</p> <p>"Plasma Wave Electronics: Novel Terahertz Devices Using Two Dimensional Electron Fluid," M. Dyakonov et al., IEEE Transactions on Electron Devices, Vol. 43, No. 10, October 1996, pp. 1640-1645.</p> <p>"A Schottky/2-DEG Varactor Diode for Millimeter and Submillimeter Wave Multiplier Applications," W. C. B. Peatman et al., The Third International Conference on Space THz Technology, Ann Arbor, MI, March 24-26, 1992, pp. 1-17.</p> <p>"Narrow Channel 2-D MESFET for Low Power Electronics," W. C. B. Peatman et al., IEEE Transactions on Electron Devices, Vol. 42, No. 9, September 1995, pp. 1569-1573.</p>		
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		*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>
	<p>"Plasma Wave Electronics for Terahertz Applications," M. Dyakonov et al., <i>Terahertz Sources and Systems, NATO Science Series II, Mathematics, Physics and Chemistry</i>, Vol. 27, 2001.</p>		
	<p>"Resonant Detection and Frequency Multiplication of Terahertz Radiation Utilizing Plasma Waves in Resonant-Tunneling Transistors," V. Ryzhii et al., <i>Journal of Applied Physics</i>, Vol. 88, No. 5, September 2000, pp. 2868-2871.</p>		
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